Silicon N Channel MOS Type (U-MOSII)/Silicon Epitaxial Schottky Barrier Diode

SSM5H01TU

DC-DC Converter

· Combined Nch MOSFET and Schottky Diode into one Package.

• Low RDS (ON) and Low VF

Absolute Maximum Ratings (Ta = 25°C) MOSFET

| Characteristics | | Symbol | Rating | Unit | |
|-------------------------|-------|--------------------------|--------|------|--|
| Drain-Source voltage | | V_{DS} | 30 | V | |
| Gate-Source voltage | | V_{GSS} | ±20 | V | |
| Drain current | DC | ΙD | 1.4 | Α | |
| | Pulse | I _{DP} (Note 2) | 2.8 | A | |
| Drain power dissipation | | P _D (Note 1) | 0.5 | W | |
| | | t = 10s | 0.8 | VV | |
| Channel temperature | | T _{ch} | 150 | °C | |

Absolute Maximum Ratings (Ta = 25°C) SCHOTTKY DIODE

| Characteristics | Symbol | Rating | Unit |
|---|------------------|-----------|------|
| Maximum (peak) reverse voltage | V_{RM} | 25 | V |
| Reverse voltage | V_{R} | 20 | V |
| Average forward current | Io | 0.5 | Α |
| Peak one cycle surge forward current (non-repetitive) | I _{FSM} | 2 (50 Hz) | Α |
| Junction temperature | Tj | 125 | °C |

1: GATE 4: CATHODE 2: SOURCE 5: DRAIN 3: ANODE UFV JEDEC — JEITA — Unit: mm

2-2R1A

Weight: 7 mg (typ.)

TOSHIBA

Absolute Maximum Ratings (Ta = 25°C) MOSFET, DIODE COMMON

| Characteristics | Symbol | Rating | Unit |
|-----------------------|---------------------------|---------|------|
| Storage temperature | T _{stg} | -55~125 | °C |
| Operating temperature | T _{opr} (Note 3) | -40~100 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board (25.4 mm \times 25.4 mm \times 1.6 t, Cu pad: 645 mm²)

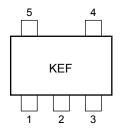
Note 2: The pulse width limited by max channel temperature.

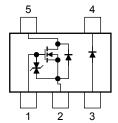
Note 3: Operating temperature limited by max channel temperature and max junction temperature.

Start of commercial production 2002-05

Marking

Equivalent Circuit





Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing and use containers and other objects that are made of anti-static materials.

The Channel-to-Ambient thermal resistance $R_{th\ (ch-a)}$ and the drain power dissipation P_D vary according to the board material, board area, board thickness and pad area. When using this device, please take heat dissipation fully into account.

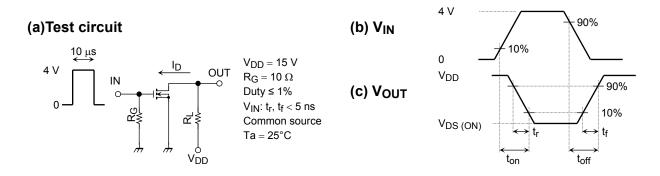
MOSFET

Electrical Characteristics (Ta = 25°C)

| Characteristic | | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|--------------------------------|---------------|----------------------|--|-----|------|-----|------|--|
| Gate leakage current | | I _{GSS} | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$ | _ | _ | ±1 | μА | |
| Drain-Source breakdown voltage | | V (BR) DSS | $I_D = 1 \text{ mA}, V_{GS} = 0$ | 30 | _ | _ | V | |
| | | V (BR) DSX | I _D = 1 mA, V _{GS} = -20 V | 15 | _ | _ | V | |
| Drain Cut-off current | | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 | _ | _ | 1 | μА | |
| Gate threshold voltage | | V_{th} | $V_{DS} = 5 \text{ V}, I_D = 0.1 \text{ mA}$ | 1.0 | _ | 2.4 | V | |
| Forward transfer admittance | | Y _{fs} | $V_{DS} = 5 \text{ V}, I_D = 0.7 \text{ A}$ (Note 4) | 0.9 | 1.8 | _ | S | |
| Drain-Source ON resistance | | R _{DS} (ON) | $I_D = 0.7 \text{ A}, V_{GS} = 10 \text{ V}$ (Note 4) | _ | 140 | 200 | - mΩ | |
| | | | $I_D = 0.7 \text{ A}, V_{GS} = 4 \text{ V}$ (Note 4) | _ | 250 | 450 | | |
| Input capacitance | | C _{iss} | V _{DS} = 15 V, V _{GS} = 0, f = 1 MHz | _ | 106 | _ | pF | |
| Reverse transfer capacitance | | C _{rss} | V _{DS} = 15 V, V _{GS} = 0, f = 1 MHz | _ | 15 | _ | pF | |
| Output capacitance | | Coss | V _{DS} = 15 V, V _{GS} = 0, f = 1 MHz | _ | 28 | _ | pF | |
| Switching time | Turn-on time | t _{on} | V _{DD} = 15 V, I _D = 0.7 A | _ | 18 | _ | no | |
| | Turn-off time | t _{off} | $V_{GS} = 0$ to 4 V, $R_G = 10 \Omega$ | _ | 10 | _ | ns | |

Note 4: Pulse measurement

Switching Time Test Circuit



Precaution

 V_{th} can be expressed as voltage between gate and source when low operating current value is ID = 100 μA for this product. For normal switching operation, V_{GS} (on) requires higher voltage than V_{th} and V_{GS} (off) requires lower voltage than V_{th} .

(Relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on))

Schottky Diode

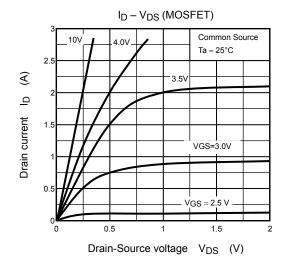
Electrical Characteristics (Ta = 25°C)

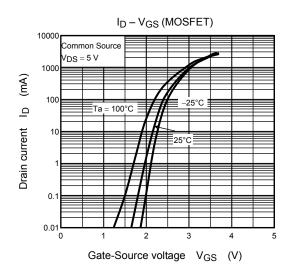
| Characteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------|--------------------|---------------------------------|-----|------|------|------|
| Forward voltage | V _{F (1)} | I _F = 0.3 A | _ | 0.38 | 0.45 | V |
| | V _{F (2)} | I _F = 0.5 A | _ | 0.43 | _ | V |
| Reverse current | I _R | V _R = 20 V | _ | _ | 50 | μΑ |
| Total capacitance | C _T | V _R = 0 V, f = 1 MHz | _ | 46 | _ | pF |

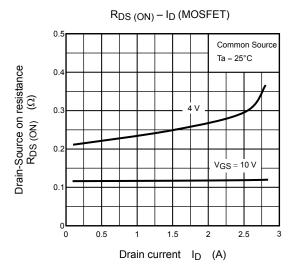
Precaution

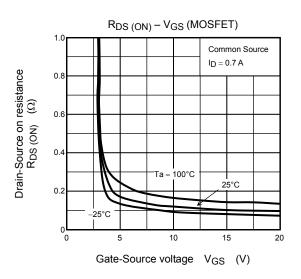
The schottky barrier diode of this product are having large-reverse-current-leakage characteristic compare to the other switching diodes. This current leakage and not proper operating temperature or voltage may cause thermal runaway. Please take forward and reverse loss into consideration when you design.

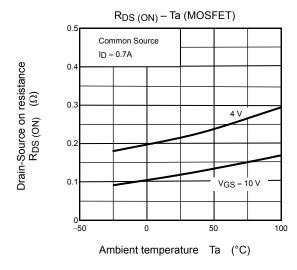
MOSFET Electrical Characteristics Graph

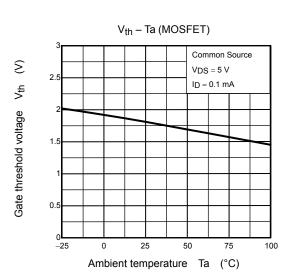


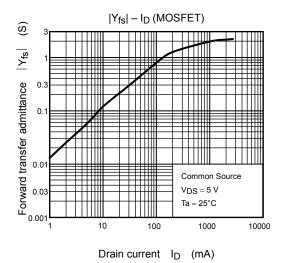


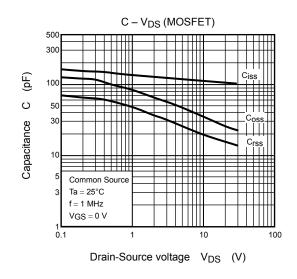


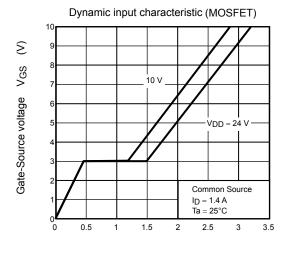




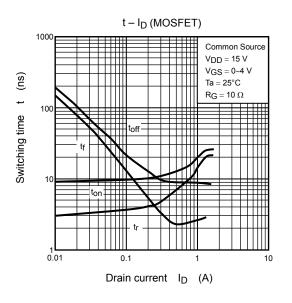


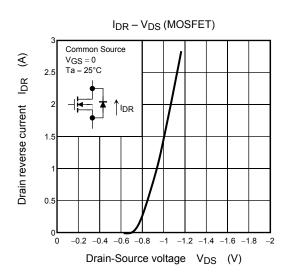




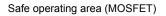


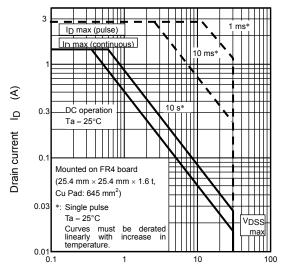
Total gate charge $\ Q_g\ (nC)$



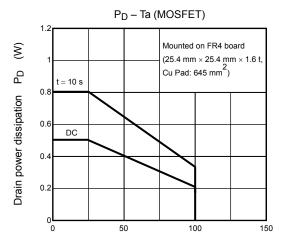


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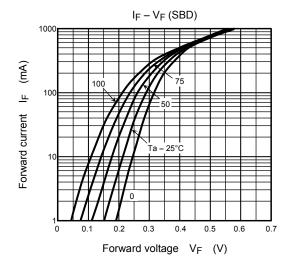
Drain-Source voltage V_{DS} (V)

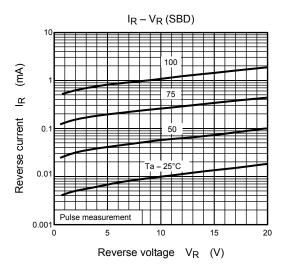


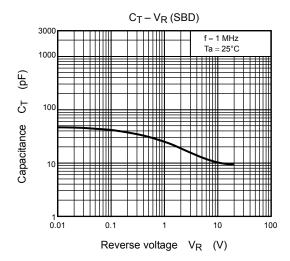
Ambient temperature Ta (°C)

7

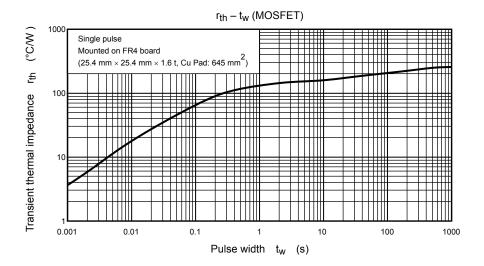
SBD Electrical Characteristics Graph

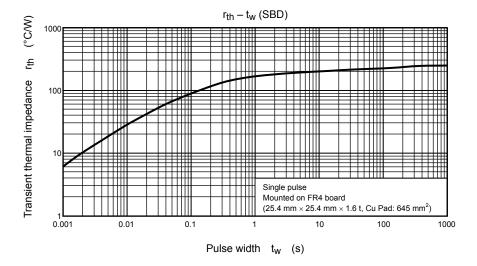






Transient thermal impedance Graph





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